

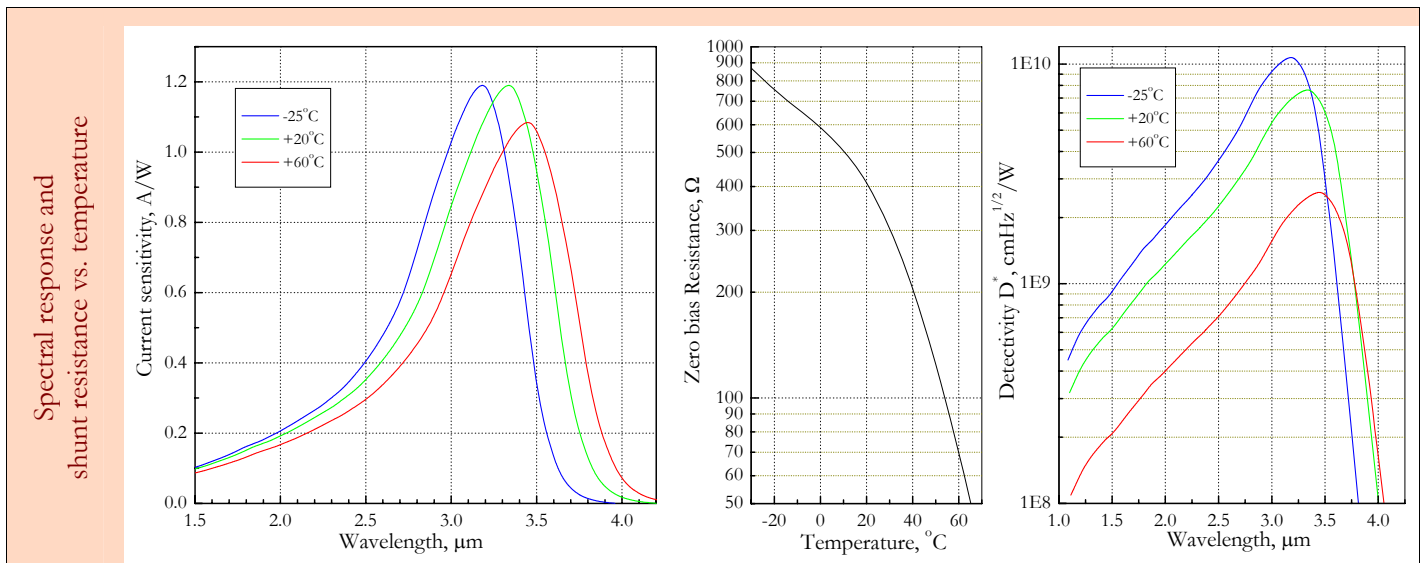
InAs photodiode

PD33fsi series

Peak wavelength	λ	μm	3.35 ± 0.05
Spectral response range	$\lambda_{0.1}$	μm	$1.75 \div 3.8$
Current sensitivity	S_I	A/W	≥ 1.2
Resistance at zero bias	R_0	Ohm	≥ 400
Detectivity	$D^*_{\lambda_{\text{max}}}$	$\text{cmHz}^{1/2}\text{W}^{-1}$	$\geq 6 \times 10^9$
Voltage sensitivity	S_U	V/W	≥ 480
Switching time	τ	ns	< 20

Model	Package	Cap with window	Sensitive area, mm	Angle of view FWHM, deg.	Operation conditions, °C	Polarity
PD33fsiTO18	TO18 (TO46)	-		140		
PD33fsiTO18c	TO18 (TO46)	Sapphire	0.33×0.33	50	-25÷+60	Short leg is negative
PD33fsiTO39c	TO39	Sapphire or quartz		90		

	PD33fsiTO18	PD33fsiTO18c	PD33fsiTO39c
Product view			
Features	Growth of narrow gap semiconductor alloys onto n ⁺ -InAs substrate; "Wide gap" window		Ambient and high temperature operation; No bias required; Short time constant; High value of shunt resistance; Operation from DC to VHF; Highest long term stability
	<p>Data are valid for 22°C. Photodiode could be equipped with preamplifier that is designed for conversion of PD photocurrent into a convenient output voltage and is adjusted for the particular PD taking into account the R_o value and frequency range.</p> <p>Other packages are available upon request</p>		



Product specifications are subject to change without prior notice due to improvements or other reasons. Updated 14.10.11



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